FNK P-Channel Enhancement Mode Power MOSFET

DESCRIPTION

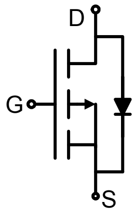
The FNK3407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

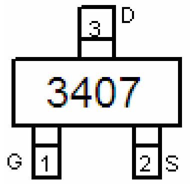
- V_{DS} = -30V,I_D = -4.1A
  $R_{DS(ON)}$ < 95mΩ @ V_{GS}=-4.5V
  $R_{DS(ON)}$ < 65mΩ @ V_{GS}=-10V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment

SOT-23 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407	FNK3407	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-4.1	A
Drain Current-Pulsed (Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	℃/W

Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V	-	-	-1	μA

Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-4.1A	-	55	65	mΩ
		V_{GS}=-4.5V, I_D=-4A	-	75	95	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-4.1A	5.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{Iss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	700	-	PF
Output Capacitance	C_{oss}		-	120	-	PF
Reverse Transfer Capacitance	C_{rss}		-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V,R_L=3.6Ω V_{GS}=-10V,R_{GEN}=3Ω	-	9	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	13.5	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-4A,V_{GS}=-10V	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	3.1	-	nC
Gate-Drain Charge	Q_{gd}		-	3.	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-1A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

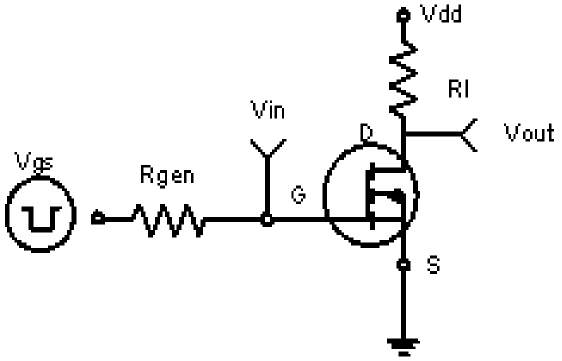


Figure 1:Switching Test Circuit

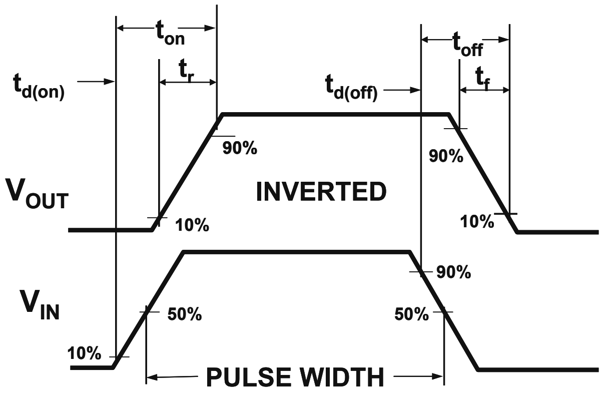


Figure 2:Switching Waveforms

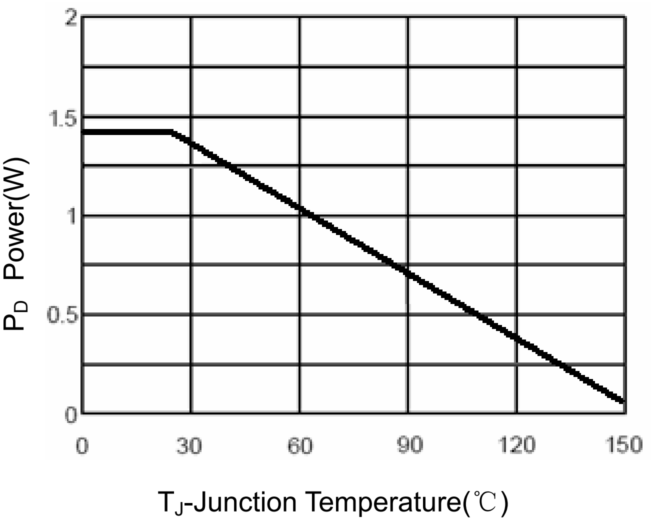


Figure 3 Power Dissipation

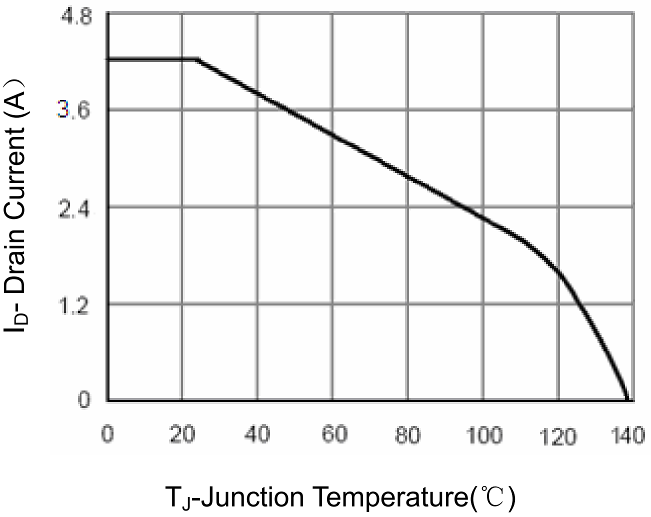


Figure 4 Drain Current

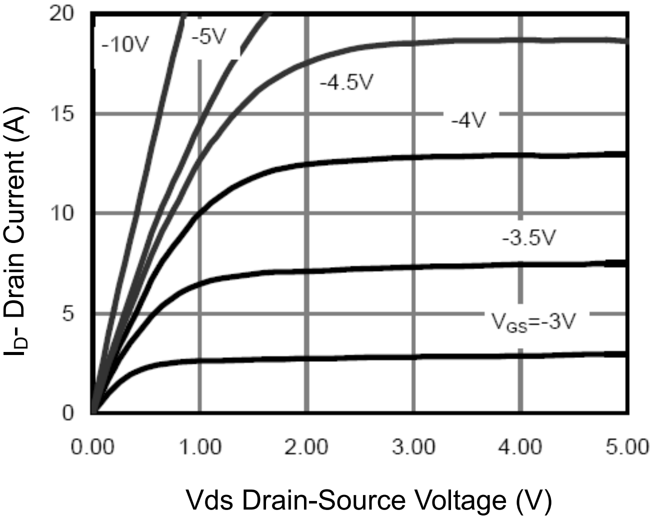


Figure 5 Output CHARACTERISTICS

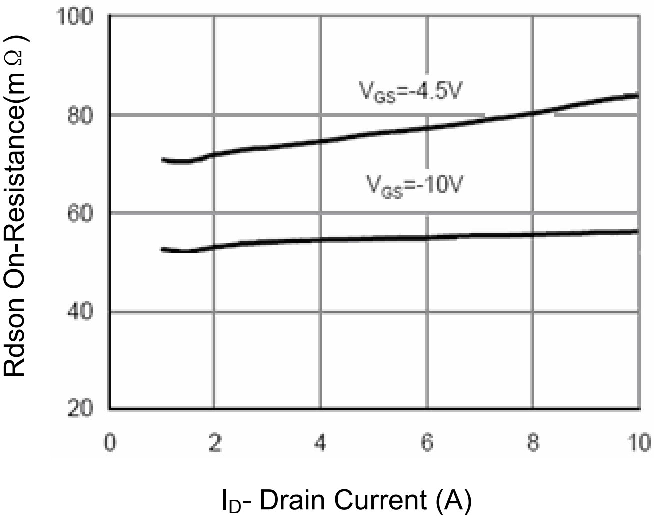


Figure 6 Drain-Source On-Resistance

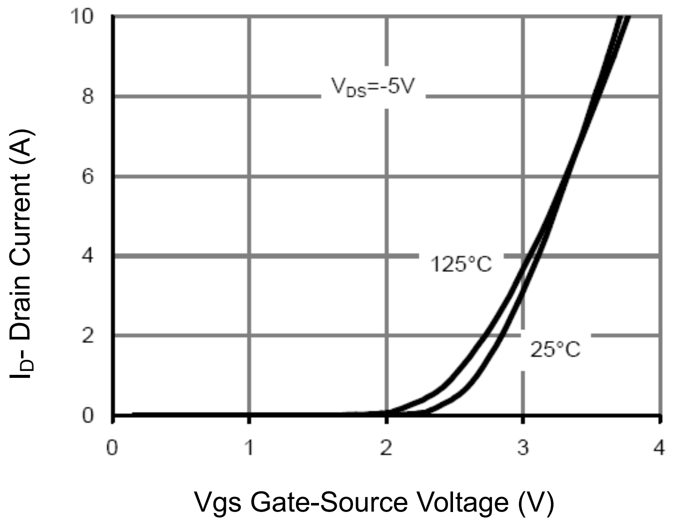


Figure 7 Transfer Characteristics

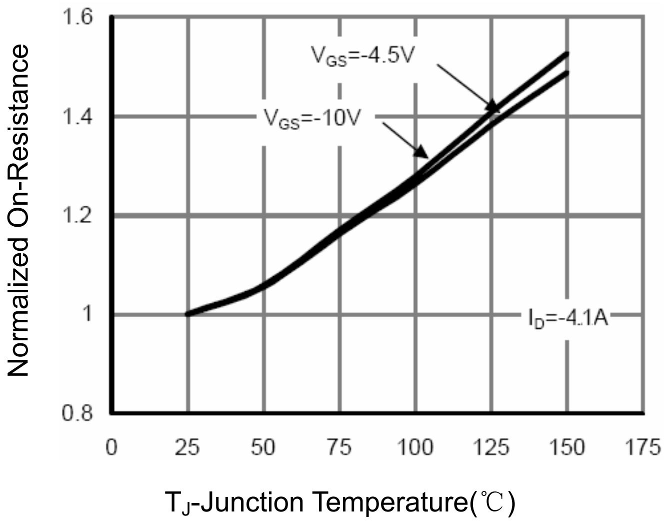


Figure 8 Drain-Source On-Resistance

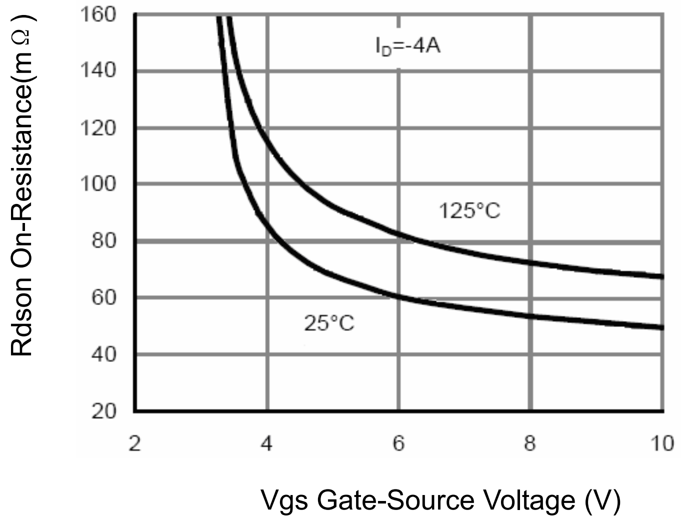


Figure 9 Rdson vs Vgs

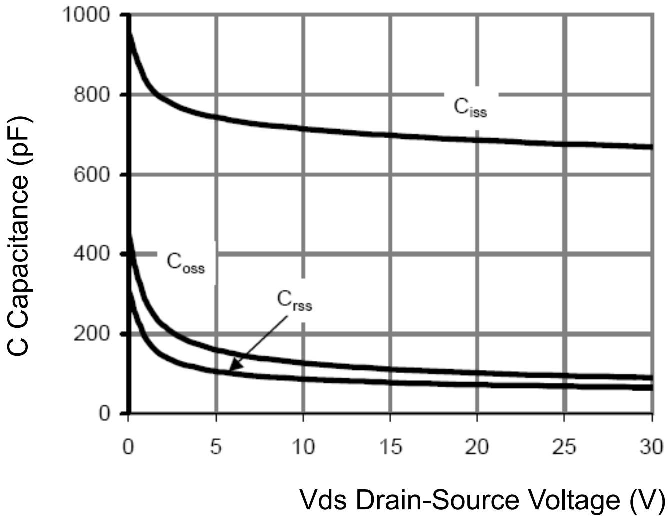


Figure 10 Capacitance vs Vds

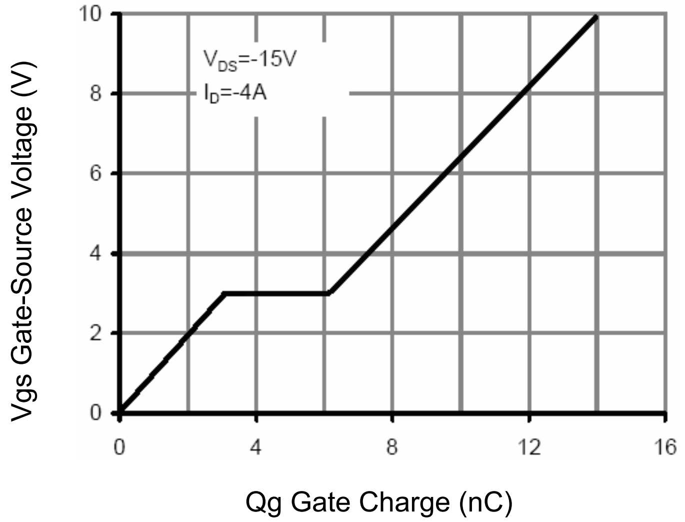


Figure 11 Gate Charge

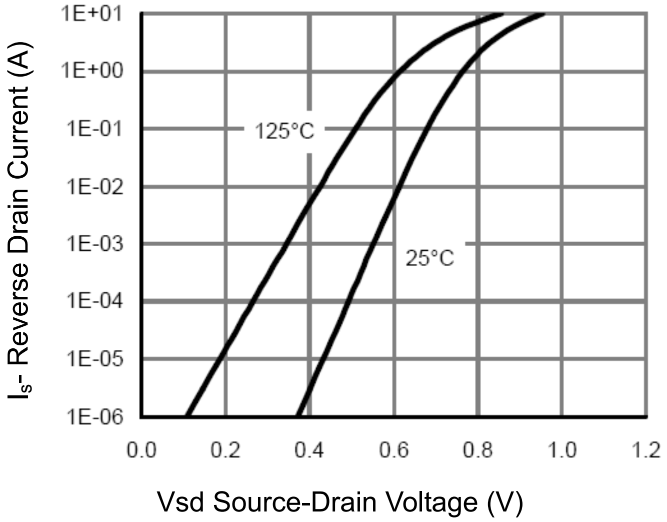
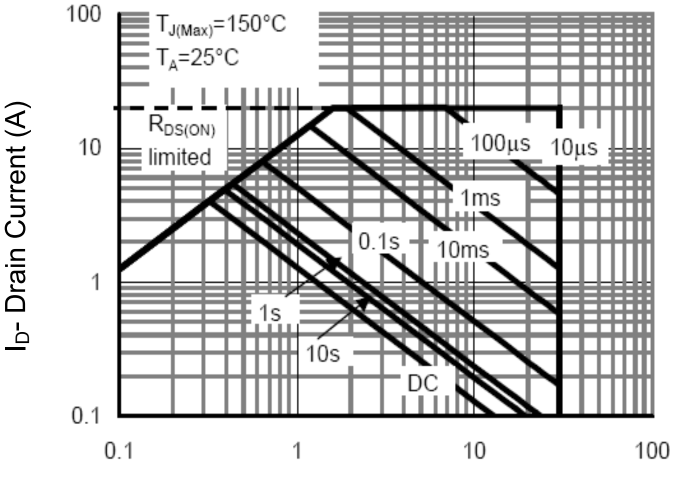
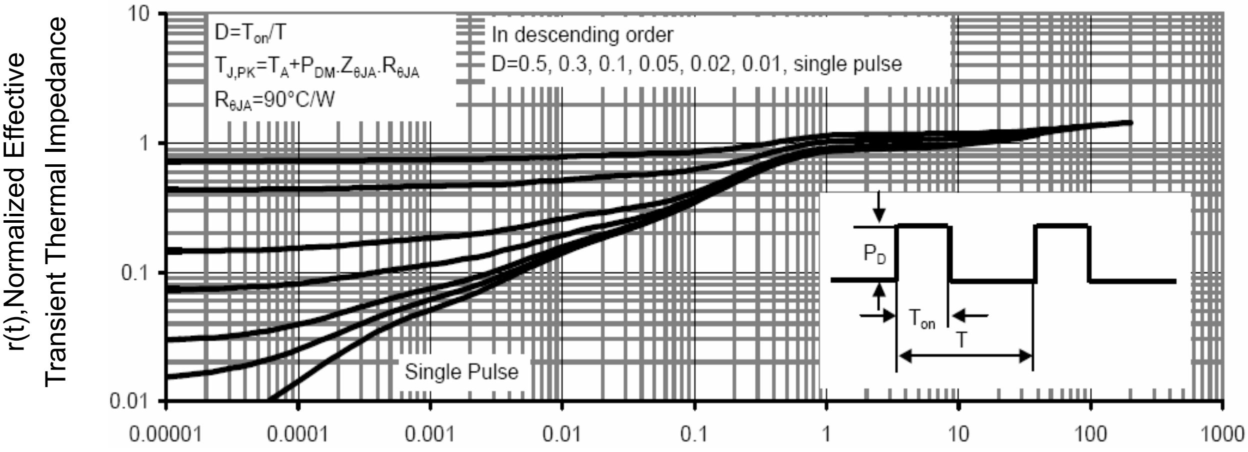


Figure 12 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

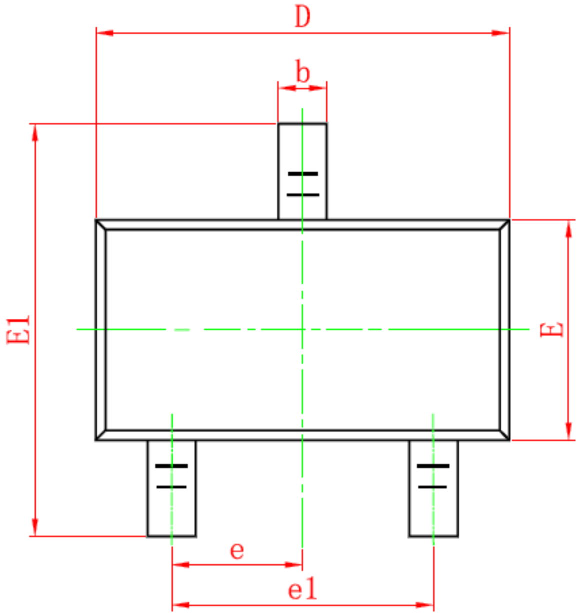


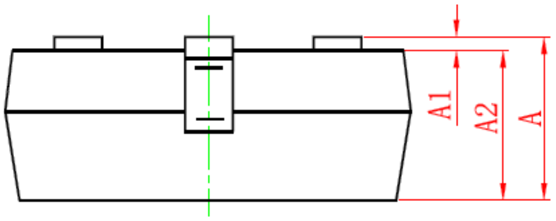
Square Wave Pluse Duration(sec)

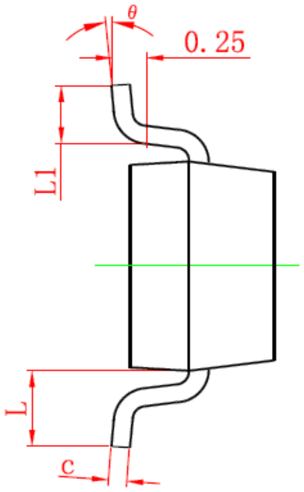
Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)







Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

NOTES

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.